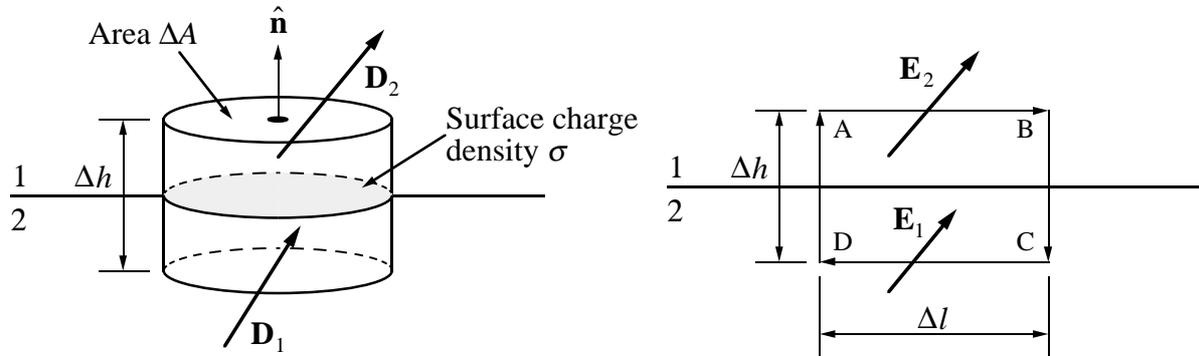


Electrostatic Boundary Conditions



Consider a Gaussian pill-box at the interface between two different media, arranged as in the figure above. The net enclosed (free) charge Q_f is

$$Q_f = \sigma\Delta A + \frac{1}{2}(\rho_1 + \rho_2)\Delta A\Delta h$$

so as the height of the pill-box Δh tends to zero the term arising from the bulk charge densities ρ_1, ρ_2 becomes negligible. The integral form of Gauss's law then tells us that

$$(\mathbf{D}_2 \cdot \hat{\mathbf{n}})\Delta A - (\mathbf{D}_1 \cdot \hat{\mathbf{n}})\Delta A \approx \sigma\Delta A$$

which becomes exact in the limit $\Delta A \rightarrow 0$ when

$$(\mathbf{D}_2 - \mathbf{D}_1) \cdot \hat{\mathbf{n}} = \sigma$$

therefore if there is no free surface charge the component of \mathbf{D} normal to the interface is continuous.

Since \mathbf{E} is a conservative field and $\oint_{ABCD} \mathbf{E} \cdot d\mathbf{l} = 0$ so

$$\text{as } \Delta h \rightarrow 0 \quad \text{so} \quad (\mathbf{E}_{2\parallel}\Delta l - \mathbf{E}_{1\parallel}\Delta l) \rightarrow 0$$

and therefore the component of \mathbf{E} tangential to the interface is continuous across the interface.

There is no reason to suspect that \mathbf{E} becomes infinite at the boundary and so the potential is continuous across the interface as a consequence of its definition.

Example: A parallel plate capacitor has plates of area A , and has the space between them entirely filled by two slabs, also of area A , of different dielectric material of thickness a and b respectively. Ignore edge-effects and find the capacitance of this structure.

Solution: Given the symmetry of the system, and the instruction to ignore edge-effects, the fields have components only normal to the interfaces which are assumed to be horizontal. When there is a potential difference V between the top and bottom plate, the work needed per unit charge to move a small test charge between them is

$$aE_A + bE_B = V.$$

The component of \mathbf{D} normal to an interface is continuous when there is no *free* charge present, as is the case at the interface between the two types of dielectric, so $D_A = D_B$ and from the definition of relative permittivity

$$D_A = \epsilon_0 \epsilon_{rA} E_A \quad \text{and} \quad D_B = \epsilon_0 \epsilon_{rB} E_B.$$

These equations are sufficient to determine the fields, for example

$$E_A = \frac{\epsilon_{rB}}{\epsilon_{rA}} E_B \quad \text{so} \quad a \frac{\epsilon_{rB}}{\epsilon_{rA}} E_B + b E_B = V \quad \Rightarrow \quad E_B = \frac{V \epsilon_{rA}}{a \epsilon_{rB} + b \epsilon_{rA}}.$$

At the interface between the lower metal plate and the dielectric B there is a surface free-charge density σ present causing a discontinuity in \mathbf{D} given by

$$(D_B - D_{\text{Metal}}) = \sigma$$

Since when the plates have a vacuum between them $D_{\text{Metal}}=0$ is required give the correct value for the capacitance and we assume that this is generally the case, hence the net charge on the lower plate Q is

$$Q = A(\epsilon_0 \epsilon_{rB} E_B - 0) = \frac{AV \epsilon_{rA} \epsilon_0 \epsilon_{rB}}{a \epsilon_{rB} + b \epsilon_{rA}}$$

and the capacitance C is therefore

$$C = \frac{Q}{V} = \frac{A \epsilon_0 \epsilon_{rA} \epsilon_{rB}}{a \epsilon_{rB} + b \epsilon_{rA}}.$$